

PRODUCT CHARACTERISTICS

V_{DS}	60
$R_{DS(ON)}$ Typ(@ $V_{GS}=10V$)	4.8m Ω
Q_g @typ	90.3nC
I_D	80A

APPLICATIONS

- * Electronic lamp ballasts based on half bridge
- * Load Switching, Quick/Wireless Charge.
- * Motor Driving

FEATURE

- * Low Gate Charge
- * Pb-Free Lead Plating



ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT80N06D	TO-252	2500 pieces/Reel

ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

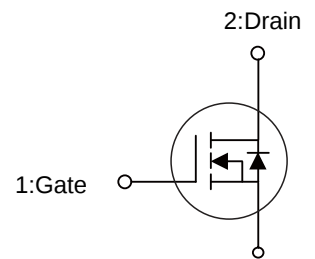
Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current Continuous(@ $V_{GS}=10V, T_A=25^{\circ}C$)	I_D	80	A
Drain Current Continuous(@ $V_{GS}=10V, T_A=100^{\circ}C$)	I_D	50	A
Drain Current Pulsed	I_{DM}	320	A
Avalanche Energy *	E_{AS}	380	mJ
Power Dissipation	P_D	65	W
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	1.9	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

Symbol



3:Source



TO-252

■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V,I _D =250μA	60	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{GS} =+20V,V _{DS} =0V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{GS} =-20V ,V _{DS} =0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =20 A	-	4.8	6	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =250μA	2	3.0	4	V
Dynamic characteristics						
Gate capacitance	R _g	V _{GS} =0V,V _{DS} =0V ,f=1.0MHz	-	0.78	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =5V,I _D =5A	-	16	-	S
Input Capacitance	C _{iss}	V _{DS} =20V,V _{GS} =0V f=1.0MHz	-	4800	-	pF
Output Capacitance	C _{oss}		-	320	-	pF
Reverse Transfer Capacitance	C _{rss}		-	310	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =30V, I _D =20 A ,R _G =3Ω	-	8.5	-	ns
Rise Time	t _r		-	7	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	40	-	ns
Fall Time	t _f		-	15	-	ns
Total Gate Charge	Q _g	I _D =20 A, V _{DS} =30V V _{GS} =10V	-	90.3	-	nC
Gate to Source Charge	Q _{gs}		-	10.9	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	20.6	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	80	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	320	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.72	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =20 A, T _J =25℃ dI /dt=100A/μs	-	32	-	ns
Reverse Recovery Charge	Q _{rr}		-	45	-	nC

■ TYPICAL CHARACTERISTICS

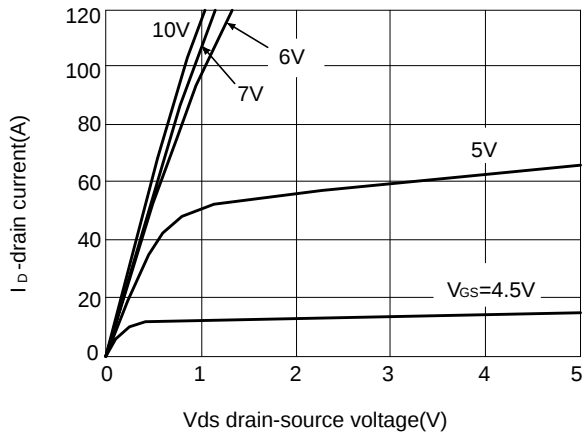


Figure 1: Output characteristics

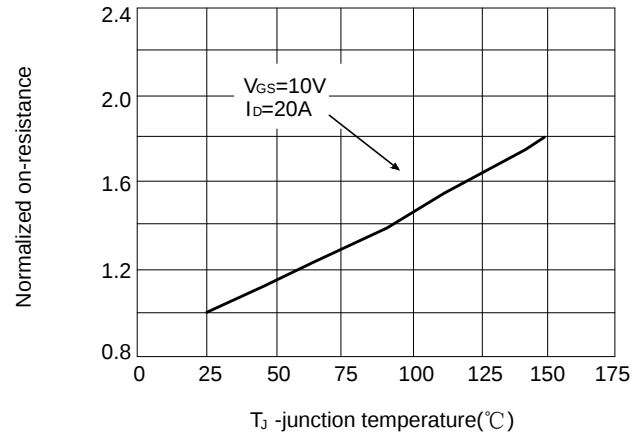


Figure 2: Rdson-junction temperature

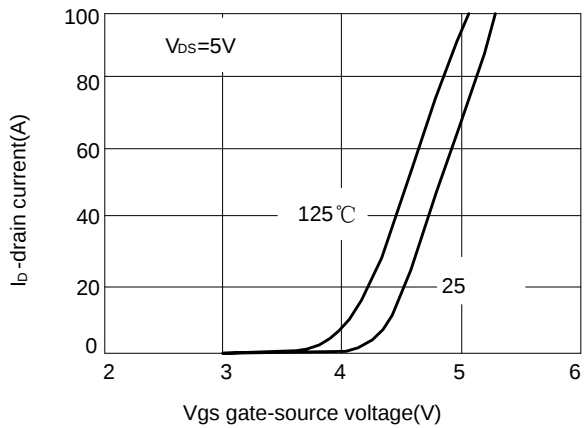


Figure 3: Transfert characteristics

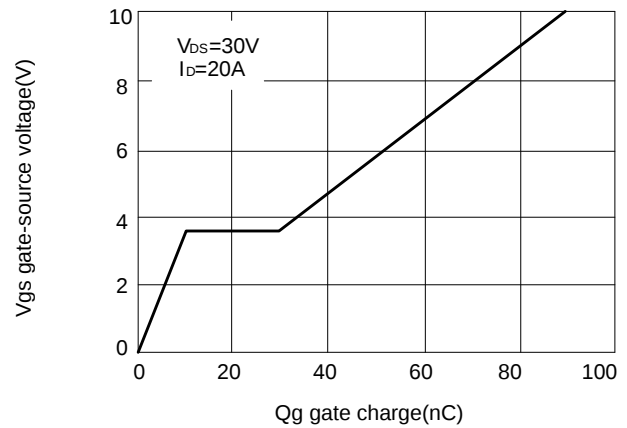


Figure 4: Gate charge

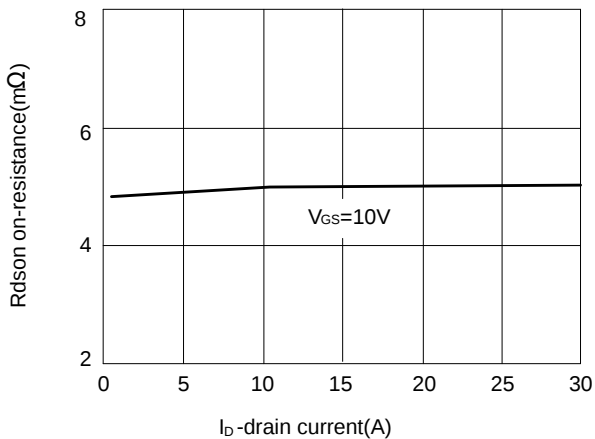


Figure 5: Rdson-drain current

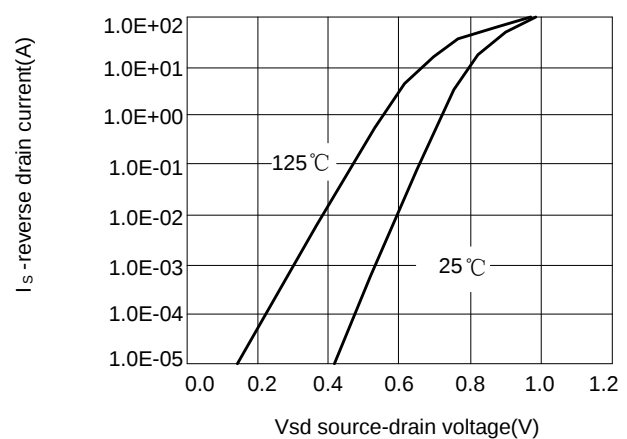


Figure 6: Source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

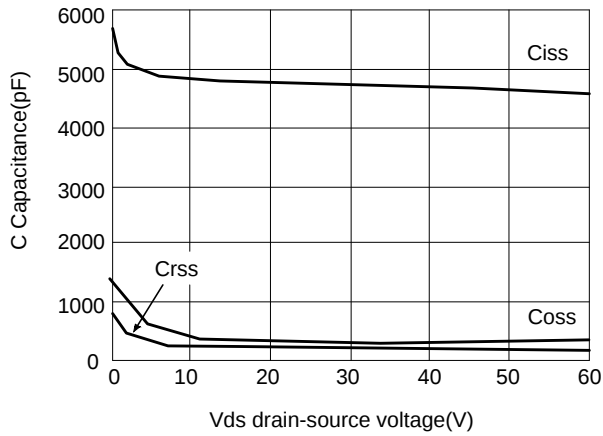


Figure 7: Capacitance vs vds

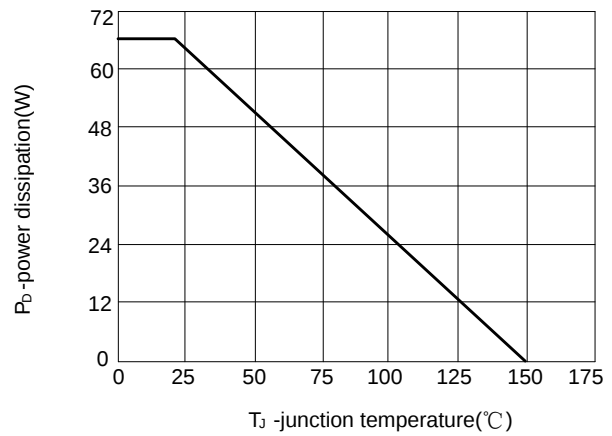


Figure 8: Power de-rating

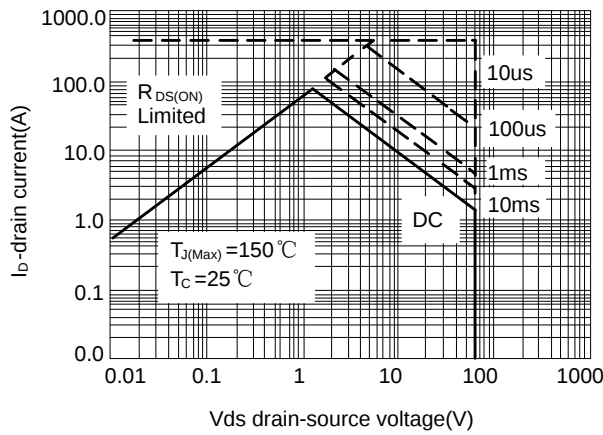


Figure 9: Safe operation area

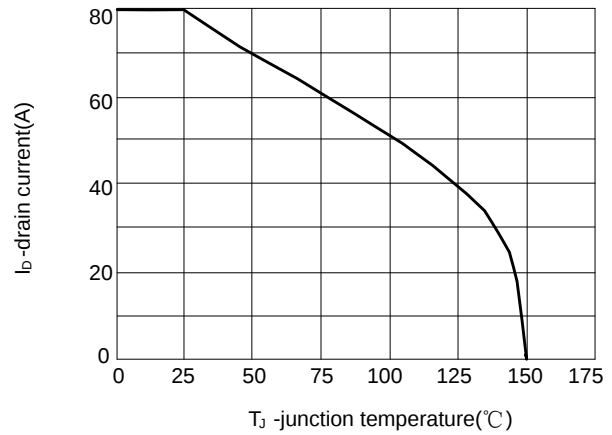


Figure 10: ID current-junction temperature

■ TO-252 PACKAGE OUTLINE DIMENSIONS

